# multicomp PRO



## RoHS Compliant

NPN 3. COLLECTOR

1. EMITTER

2. BASE

### **Absolute Maximum Ratings**

Description	Symbol	Value	Unit
Collector Emitter Voltage, $R_{BE} \le 10\Omega$	Vcer	50	V
Collector Base Voltage	Vсво	75	V
Emitter Base Voltage	Vebo	7	V
Power Dissipation at T <sub>A</sub> = 25°C Derate above 25°C	PD	800 4.57	mW mW/°C
Power Dissipation at Tc = 25°C Derate Above 25°C	PD	3 17.15	W mW/°C
Operating and Storage Junction Temperature Range	Tj, Tstg	- 65 to +200	°C

### Electrical Characteristics: (T<sub>A</sub> = +25°C Unless otherwise specified)

Description	Symbol	Test Conditions	Min	Мах	Unit
Collector Emitter Voltage	VCER	lc = 1mA, R <sub>BE</sub> ≤ 10Ω	50		V
Collector Base Voltage	Vсво	Ic = 100μA, Iε = 0	75		V
Emitter Base Voltage	Vebo	Iε = 100μA, Ic = 0	7		V
Collector Cutoff Current	Ісво	Vcb = 60V, Ie = 0 Vcb = 60V, Ie = 0, Ta = 150°C		10 10	nA µA
Emitter Cutoff Current	Іево	VEB =5V, IC = 0		5	nA
DC Current Gain	hfe	Ic = 0.01mA, Vce = 10V Ic = 0.1mA, Vce =10V Ic = 10mA, Vce =10V Ic=10mA, Vce=10V, Ta= -55°C Ic = 150mA, Vce = 10V Ic = 150mA, Vce = 10V	20 35 75 35 100 40	300	
Collector Emitter Saturation Voltage	*VCE(Sat)	Ic = 150mA, Iв = 15mA		0.5	V
Base Emitter Saturation Voltage	*VBE(Sat)	Ic = 150mA, Iв = 15mA		1.3	V

#### Small Signal Characteristics

Description	Symbol	Test Conditions	Min	Max	Unit
Transition Frequency	f⊤	Ic=50mA, Vc==10V, f=20MHz	70		MHz
Output Capacitance	Cob	Vcb = 10V, IE = 0, f = 100kHz		25	pF
Input Capacitance	Cib	V <sub>EB</sub> = 0.5V, Ic = 0, f = 100kHz		80	рF

Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro



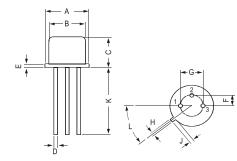
## NPN Silicon Planar Transistor 50VCE0

# multicomp PRO

Description	Symbol	Test Conditions	Min	Мах	Unit
Input Impedance	hib	Ic = 1mA, Vcв = 5V, f = 1kHz Ic = 5mA, Vcв = 10V, f = 1kHz	24 4	34 8	Ω Ω
Voltage Feedback Ratio	hrb	Ic = 1mA, Vсв = 5V, f = 1kHz Ic = 5mA, Vсв = 10V, f = 1kHz		5 5	x10 <sup>-4</sup> x10 <sup>-4</sup>
Small Signal Current Gain	h <sub>fe</sub>	Ic = 1mA, Vcв = 5V, f = 1kHz Ic = 5mA, Vcв = 10V, f = 1kHz	50 70	200 300	
Output Admittance	hob	Ic = 1mA, Vcв = 5V, f = 1kHz Ic = 5mA, Vcв = 10V, f = 1kHz	0.05 0.05	0.05 0.05	µmhos µmhos
Noise Figure	NF	Ic = 300mA, Vce = 10V, f = 1kHz		8	dB

\*Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle < 2%

#### TO-39 Metal Can Package



Dim.	Min.	Max.
А	8.5	9.39
В	7.74	8.50
С	6.09	6.60
D	0.4	0.53
E	-	0.88
F	2.41	2.66

Dim.	Min.	Max.
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
К	12.7	-
L	42 Deg.	48 Deg.

**Dimensions : Millimetres** 

#### **Part Number Table**

Description	Part Number	
NPN Silicon Planar Transistor, 50V, TO-39	MP001165	

Important Notice : This data sheet and its contents (the "Information") belong to the members of the AVNET group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp Pro is the registered trademark of Premier Farnell Limited 2019.

Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro

